



#### 175°C P-CHANNEL ENHANCEMENT MODE MOSFET **POWERDI**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C
-30V	7.5mΩ @ V <sub>GS</sub> = -10V	-60A
-30 V	10mΩ @ V <sub>GS</sub> = -4.5V	-50A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- **Power Management Functions**
- Reverse Polarity Protection

### **Features and Benefits**

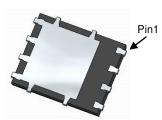
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP Capable (Note 4)**

#### **Mechanical Data**

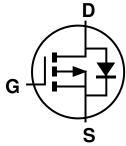
- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.097 grams (Approximate)



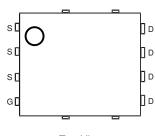




**Bottom View** 



Internal Schematic



Top View Pin Configuration

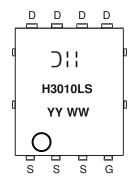
### Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH3010LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



) | | = Manufacturer's Marking H3010LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	-30	V		
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 8) V <sub>GS</sub> = -10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	-60 -40	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	I <sub>D</sub>	-15 -11	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-100	Α		
Maximum Body Diode Continuous Current (Note 7)	Is	-3.5	Α		
Avalanche Current (Note 9) L = 0.1mH	I <sub>AS</sub>	-47	Α		
Avalanche Energy (Note 9) L = 0.1mH	E <sub>AS</sub>	113	mJ		

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25$ °C	$P_D$	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	$P_D$	2.6	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	58	°C/W
Thermal Resistance, Junction to Case (Note 8)		R <sub>0JC</sub>	0.9	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

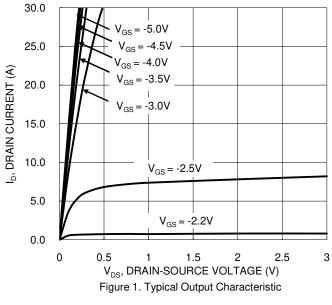
Γ							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	1	_	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	1	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Paggan	_	5.7	7.5	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Diam-Source Off-Hesistance	R <sub>DS(ON)</sub>	-	7.2	10	11122	$V_{GS} = -4.5V, I_D = -10A$	
Diode Forward Voltage	$V_{SD}$	_	-0.65	-1.0	V	$V_{GS} = 0V$ , $I_S = -1A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	6807	_	pF	15)/ )/ 0)/	
Output Capacitance	Coss	-	988	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	l	647	_	pF	1 = 1.01/11/12	
Gate Resistance	$R_g$	I	6.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	1	66	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	I	139	_	nC	\/ 15\/ I- 10A	
Gate-Source Charge	$Q_{gs}$	I	19.1	_	nC	$V_{DS} = -15V, I_{D} = -10A$	
Gate-Drain Charge	$Q_{gd}$	I	21.7	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	9.0	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	10.5	_	ns	$V_{DS} = -15V, V_{GEN} = -10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	1	255	_	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>F</sub>	1	95	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	27	_	ns	I <sub>F</sub> = -10A, di/dt = -100A/μs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	21	_	nC	I <sub>F</sub> = -10A, di/dt = -100A/μs	

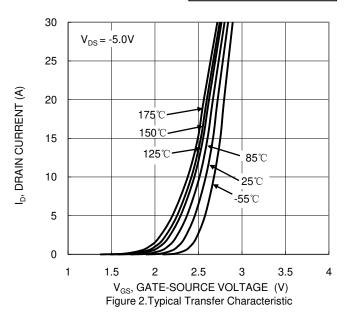
Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

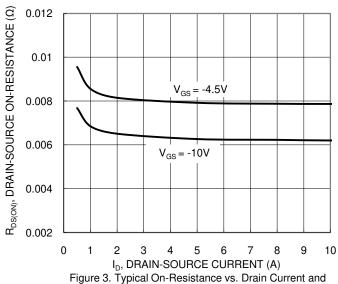
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 9.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_{J}$  = +25°C.
- 10. Short duration pulse test used to minimize self-heating effect.
- 11. Guaranteed by design. Not subject to product testing.



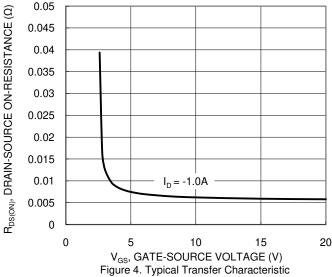


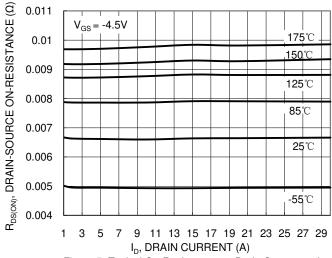






Gate Voltage





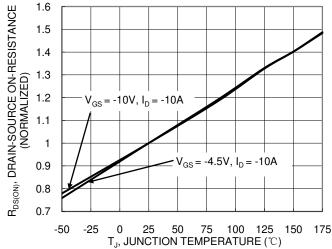
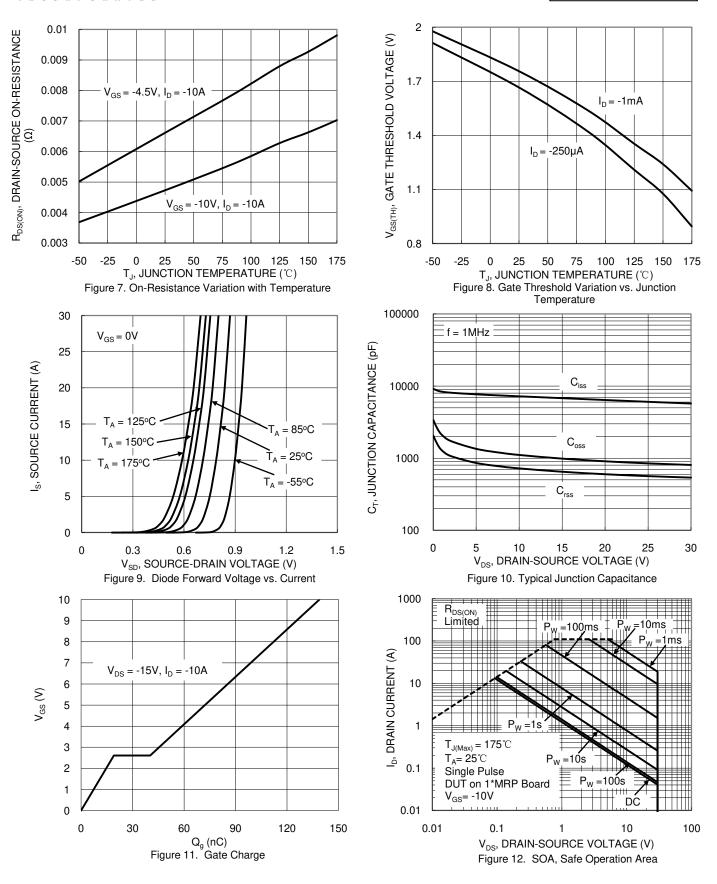


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with Temperature









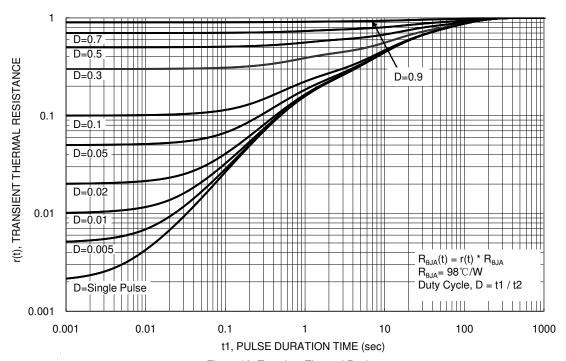


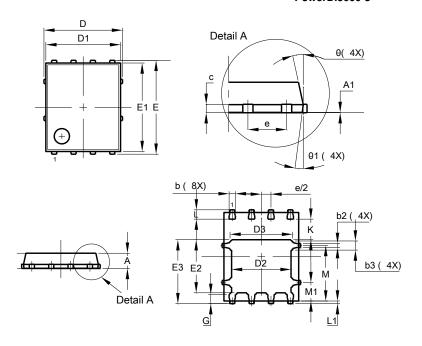
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

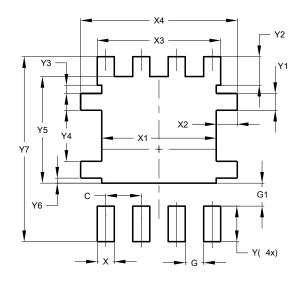


PowerDI5060-8					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	<b>3</b> 3.90 4.30 4.1		4.10		
Е		6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99 4.39 4.1		4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51 0.71 0.		0.61		
L1	0.100 0.200 0.17		0.175		
М	3.235				
M1	1.00	1.40	1.21		
Θ	10⁰	12º	11º		
Θ1	6º	8º	7º		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
Х	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Υ	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				



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